

T. Zampini et al.

Page 2

A1  
Cont

10. (amended) The method of claim 1 wherein the resin comprises halogen, halogenated lower alkyl, nitro, cyano, sulfinyl, O-C-O or sulfonyl groups.

11. (amended) The method of claim 1 wherein the resin comprises at least one of fluorine atom, fluorinated lower alkyl, perfluoroalkyl, perfluoroalkylene, fluorinated cycloalkyl, and fluorinated ethers and esters including fluorinated cyclic ethers and esters.

12. (amended) The method of claim 1 wherein the resin comprises acrylate units.

13. (amended) The method of claim 1 wherein the resin is a homopolyacetal.

14. (amended) The method of claim 1 wherein the resin is a copolyacetal.

15. (amended) The method of claim 1 wherein the polymer is chemically amplified positive resist.

16. (amended) The method of claim 1 wherein the polymer is a negative resist.

A2

18. (amended) The photoresist composition of claim 17 wherein repeat units of the polymer comprise one or more electronegative substituents.

A3

31. (amended) A method of forming a positive or negative photoresist relief image, comprising:

- (a) applying a coating layer of a photoresist of claim 17 on a substrate; and
- (b) exposing and developing the photoresist layer to yield a relief image.

A4

33. (amended) An article of manufacture comprising a substrate having coated thereon a layer of the photoresist composition of claim 17.